

750V, 56A, N-channel SiC power MOSFET
General Description:

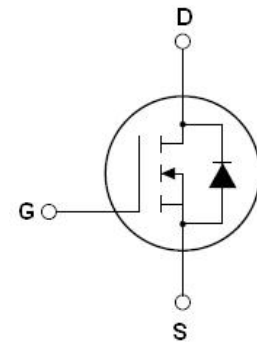
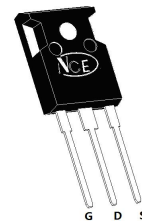
NCES075R026T is a SiC MOSFET that contributes to miniaturization and low power consumption of applications. This product achieves industry-leading low on-resistance without sacrificing short-circuit withstand time.

Features

- Low on-resistance
- Fast switching speed
- Fast reverse recovery
- Easy to parallel
- Simple to drive
- Pb-free lead plating ; RoHS compliant

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives


Schematic diagram

TO-247-3L
Package Marking and Ordering Information

Device	Device Package	Device Marking
NCES075R026T	TO-247-3L	NCES075R026T

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	750	V
Gate-Source Voltage	V _{GS}	-4 to +21	V
Drain Current-Continuous (Note 1)	I _D	56	A
Drain Current-Continuous(T _c =100°C)	I _D (100°C)	39	A
Pulsed Drain Current (Note 1)	I _{DM}	91	A
Maximum Power Dissipation	P _D	176	W
Recommended turn-on gate - source drive voltage	V _{GS_on}	+15 to +18	V
Recommended turn-off gate - source drive voltage	V _{GS_off}	0	V
Virtual junction temperature	T _{vj}	175	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-40 To 175	°C

Thermal Characteristic

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R _{θJC}	Thermal Resistance, Junction to case		0.65	0.85	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =100uA	750	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =750V, V _{GS} =0V	-	1	-	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =-4V / +21V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =10V, I _D =15.4mA	2.8		4.8	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =18V, I _D =29A	-	26	34	mΩ
Gate input resistance	R _G	f=1MHZ, open drain	-	1	-	Ω
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =29A		8		S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =500V, V _{GS} =0V, f=1MHz	-	2290	-	pF
Output Capacitance	C _{oss}		-	151	-	pF
Reverse Transfer Capacitance	C _{rss}		-	8.5	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =500V, I _D =29A V _{GS} =+18V / 0V, R _G =6.8Ω, L=250μH	-	9.5	-	ns
Turn-on Rise Time	t _r		-	22	-	ns
Turn-Off Delay Time	t _{d(off)}		-	45	-	ns
Turn-Off Fall Time	t _f		-	13	-	ns
Total Gate Charge	Q _g	V _{DS} =500V, I _D =29A, V _{GS} =18V	-	94	-	nC
Gate-Source Charge	Q _{gs}		-	20	-	nC
Gate-Drain Charge	Q _{gd}		-	23	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _D =29A	-	3.3	-	V
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =30A, V _R =800V, di/dt = 2700A/μs ^(Note3)	-	12		ns
Reverse Recovery Charge	Q _{rr}		-	141		nC
Peak reverse recovery current	I _{rrm}				24	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. PW ≤ 10μs, Duty cycle ≤ 1%
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

Fig.1-1 Gate Charge Measurement Circuit

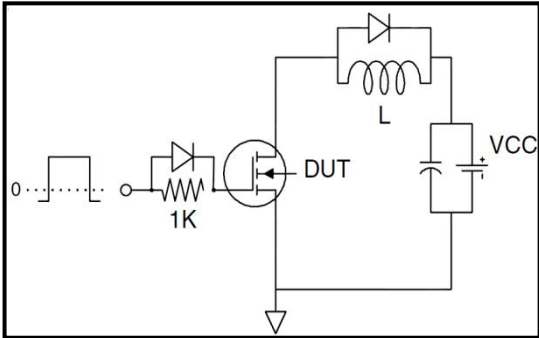


Fig.1-2 Gate Charge Waveform

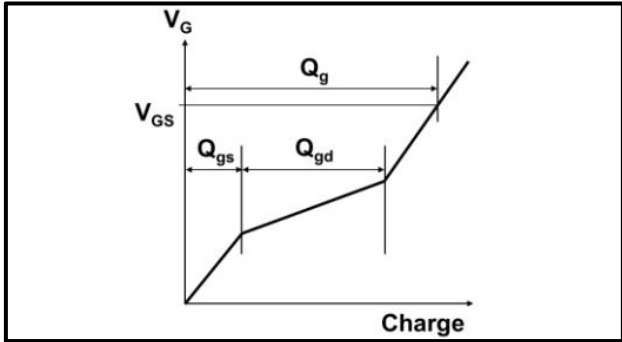


Fig.2-1 Switching Characteristics Measurement Circuit

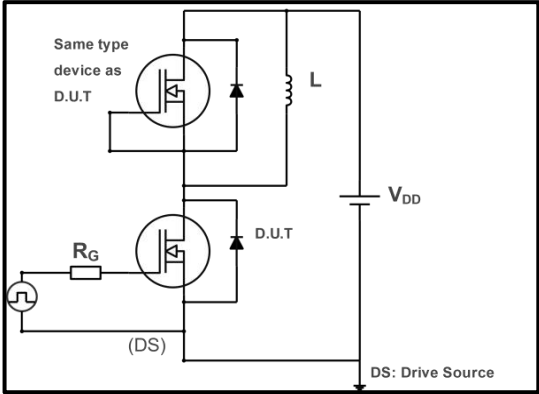
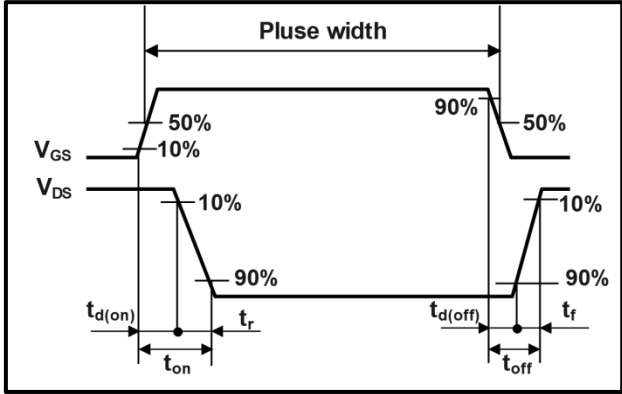


Fig.2-2 Waveforms for Switching Time



Typical Electrical and Thermal Characteristics

Fig.1 Power Dissipation Derating Curve

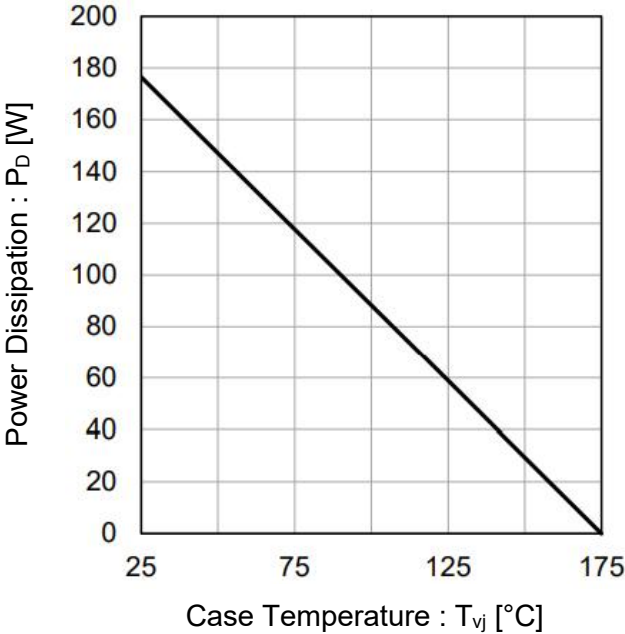


Fig.2 Maximum Safe Operating Area

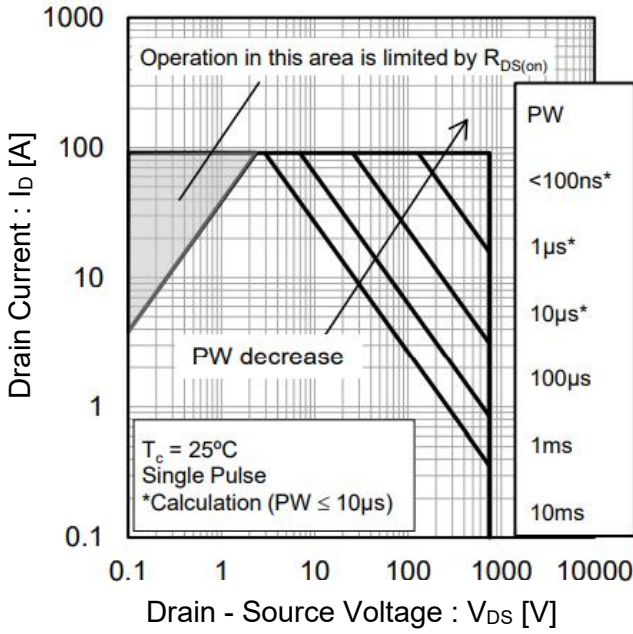


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width

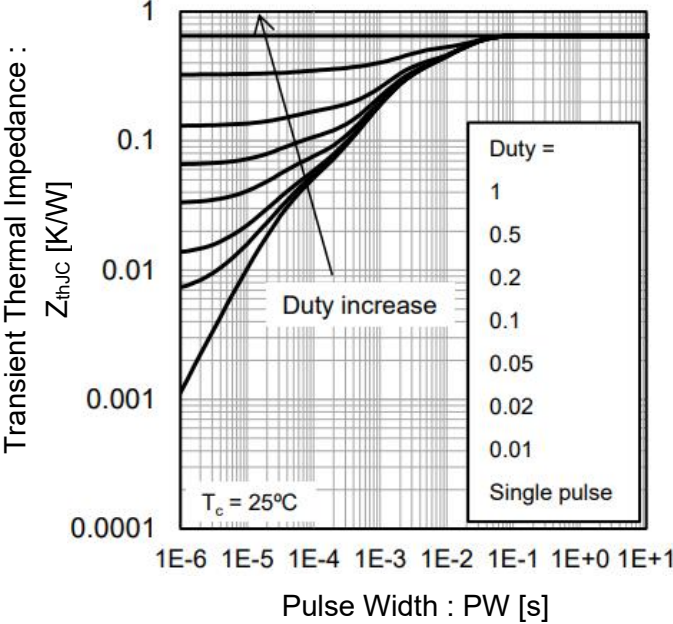


Fig.4 $T_{vj} = 25^{\circ}C$ Typical Output Characteristics

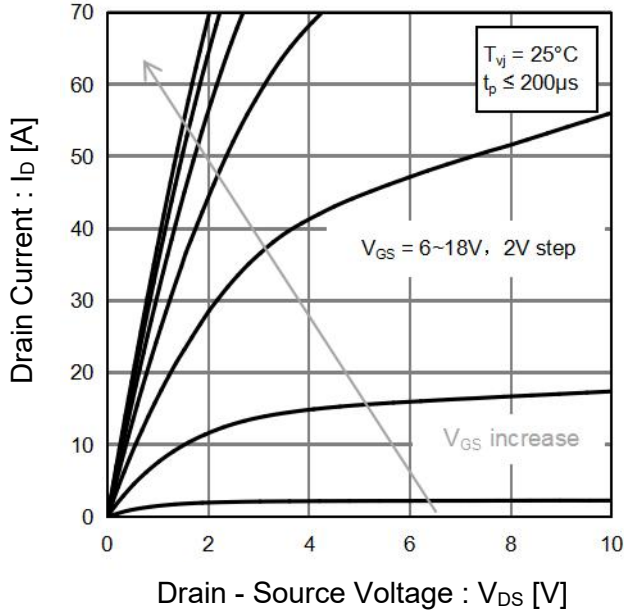


Fig.5 $T_{vj} = 25^{\circ}C$ 3rd Quadrant Characteristics

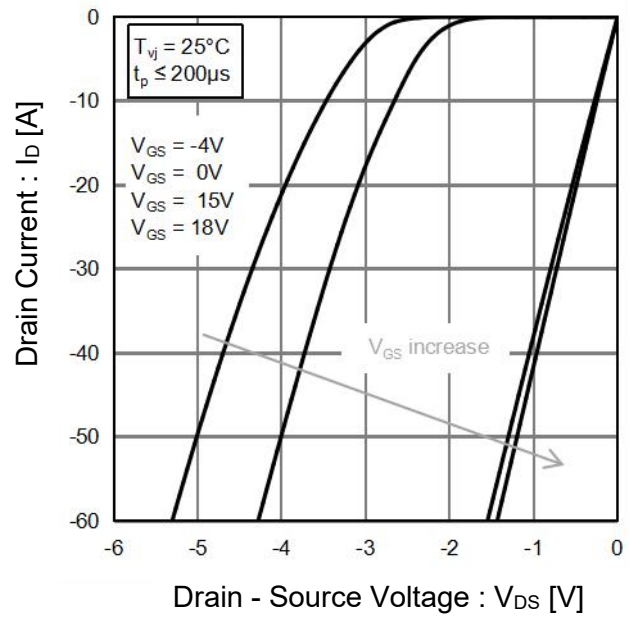


Fig.6 $T_{vj} = 150^{\circ}C$ Typical Output Characteristics

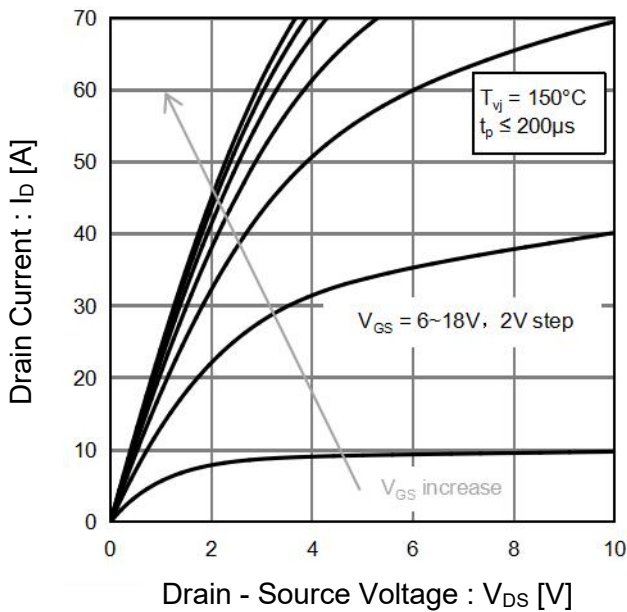


Fig.7 $T_{vj} = 150^{\circ}C$ 3rd Quadrant Characteristics

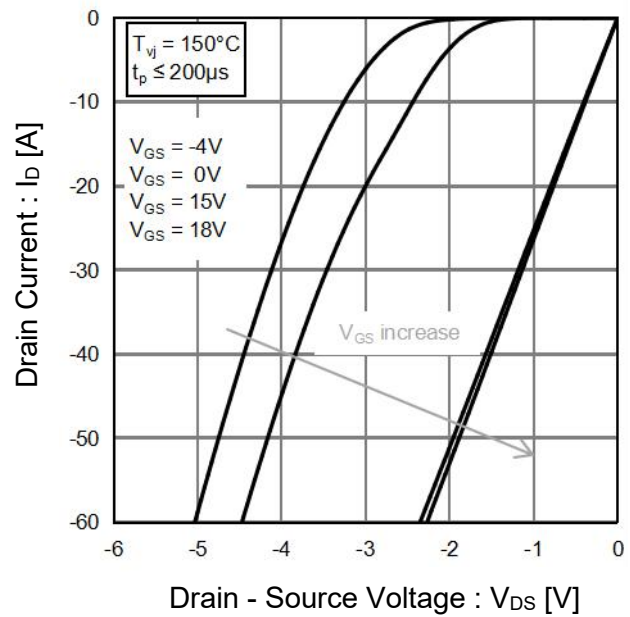


Fig.8 Typical Transfer Characteristics

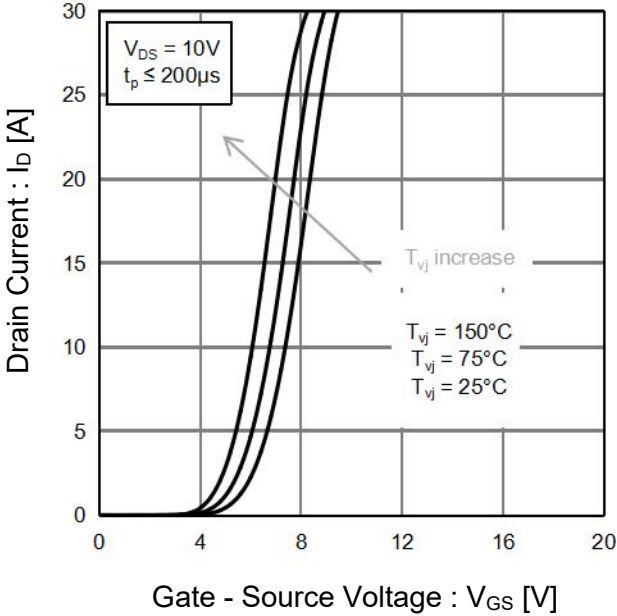


Fig.9 Body Diode Forward Voltage vs. Gate - Source Voltage

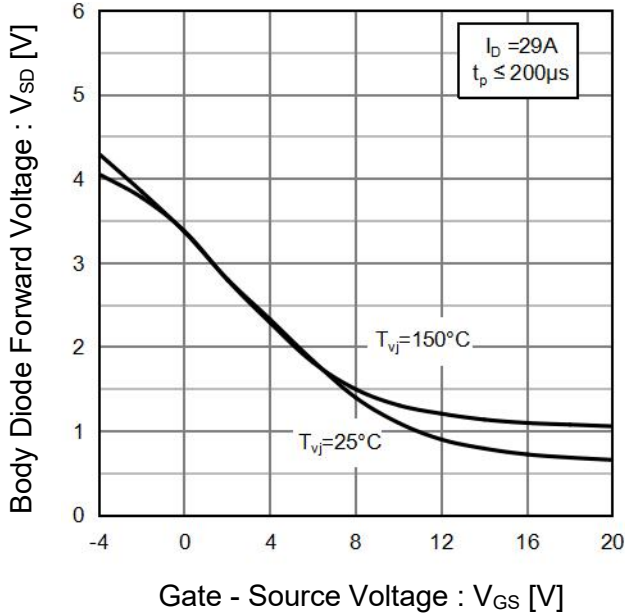


Fig.10 Gate Threshold Voltage vs. Virtual Junction Temperature

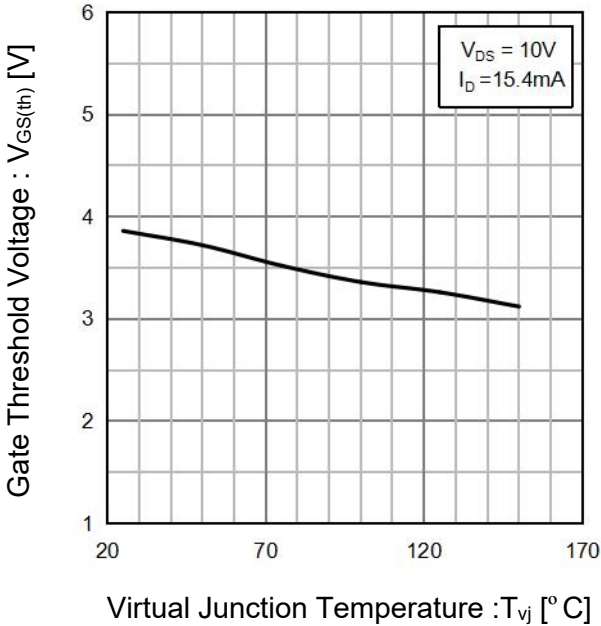


Fig.11 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

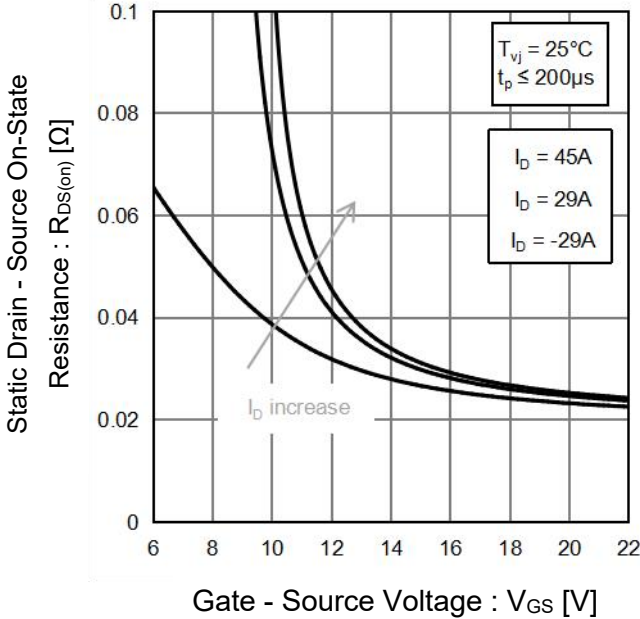


Fig.12 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

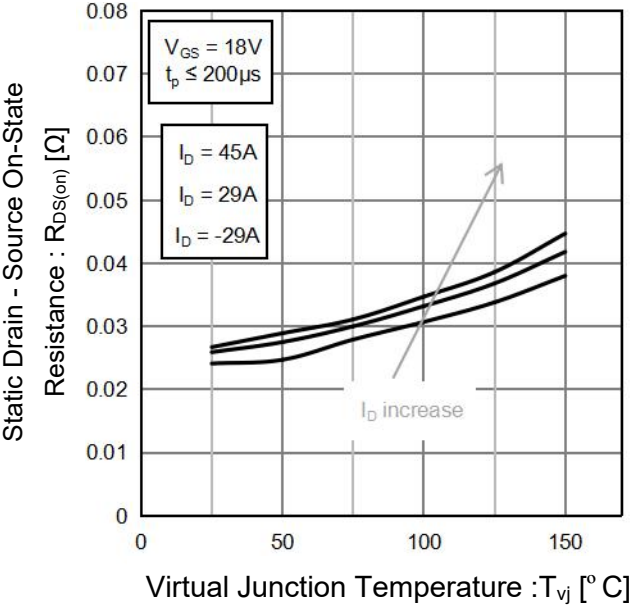


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current

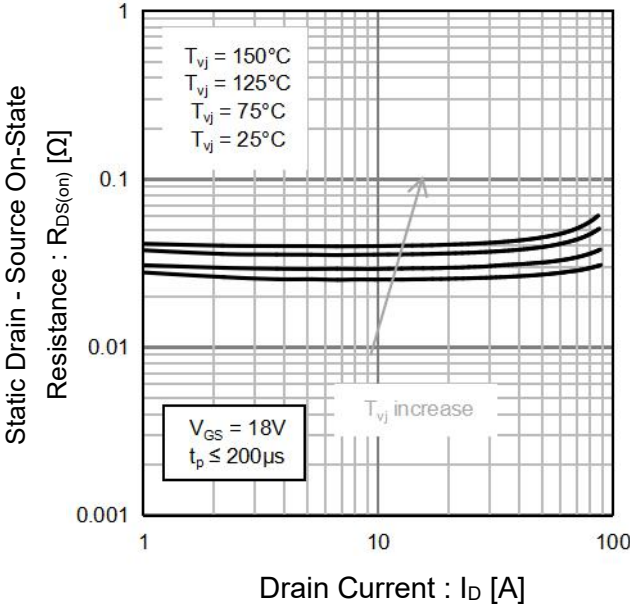


Fig.14 Typical Capacitance vs. Drain - Source Voltage

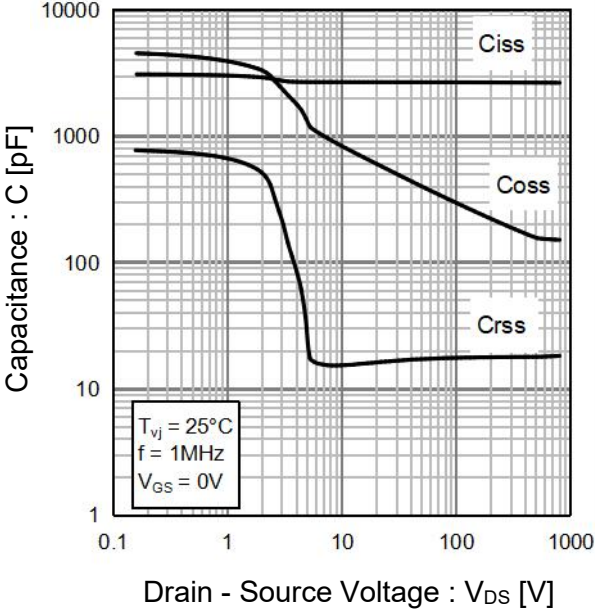
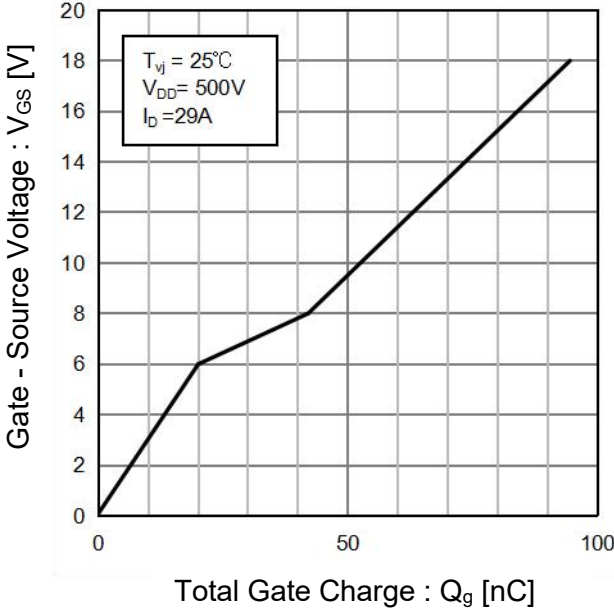
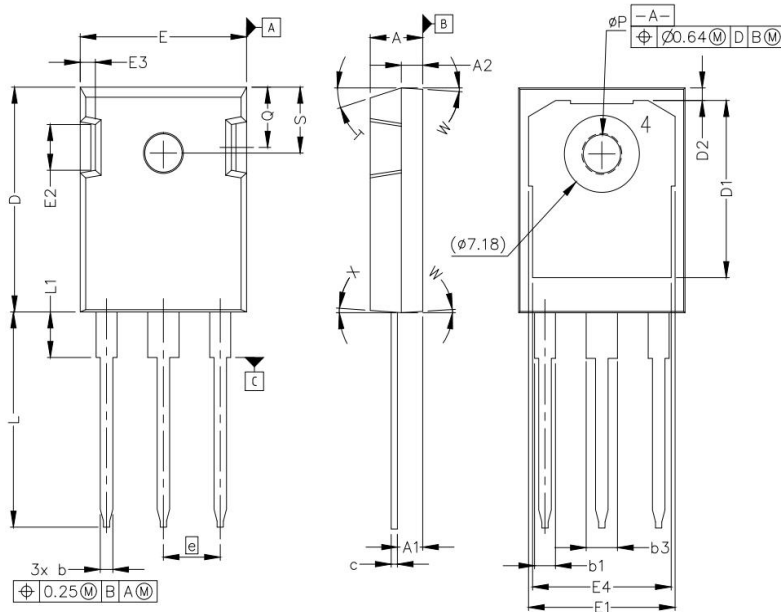


Fig.15 Dynamic Input Characteristics



TO-247-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.19	0.21
A1	2.29	2.54	0.09	0.10
A2	1.91	2.16	0.08	0.09
b	1.07	1.33	0.04	0.05
b1	1.91	2.41	0.08	0.10
b3	2.87	3.38	0.11	0.13
c	0.55	0.68	0.02	0.03
D	20.80	21.10	0.82	0.83
D1	16.25	17.65	0.64	0.70
D2	0.95	1.25	0.04	0.05
E	15.75	16.13	0.62	0.64
E1	13.10	14.15	0.52	0.56
E2	3.68	5.10	0.15	0.20
E3	1.00	1.90	0.04	0.08
E4	12.38	13.43	0.49	0.53
e	5.44 BSC		0.21 BSC	
L	19.81	20.32	0.78	0.80
L1	4.10	4.40	0.16	0.17
ØP	3.51	3.65	0.14	0.15
Q	5.49	6.00	0.22	0.24
S	6.04	6.30	0.24	0.25
T	17.5° REF			
W	3.5° REF			
X	4° REF			

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